

General Description

The SMC8205AGW is the highest performance trench

N-ch MOSFETs with extreme high cell density,

which provide excellent RDSON and gate charge

for most of the small power switching and

load switch applications. The meet the RoHS and

Product requirement with full function reliability approved.

General Features

 V_{DS} = 20V I_D = 6A

 $R_{DS(ON)} < 27m\Omega @ V_{GS}=4.5V$

 $R_{DS(ON)}$ <37m Ω @ V_{GS}=2.5V

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

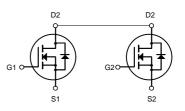
Product ID	Pack	Brand	Qty(PCS)
SMC8205AGW	TSSOP-8	HXY MOSFET	5000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

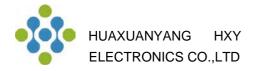
Symbol	Parameter	Limit	Unit	
Vds	Drain-Source Voltage	20	V	
Vgs	Gate-Source Voltage	±12	V	
ID	Drain Current-Continuous	6	A	
DM	Drain Current-Pulsed (Note 1)	25	A	
PD	Maximum Power Dissipation	1.5	W	
Тј,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	83	°C /W	



TSSOP-8



Dual N-Channel MOSFET



Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20 21		-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =19.5V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±10V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.7	1.2	V
		V _{GS} =4.5V, I _D =4.5A	-	21	27	mΩ
Drain-Source On-State Resistance	Rds(on)	V _{GS} =2.5V, I _D =3.5A	-	27	37	mΩ
Forward Transconductance	gfs	V _{DS} =5V,I _D =4.5A	-	10	-	S
Input Capacitance	C _{lss}		-	600	-	PF
Output Capacitance	Coss	V _{DS} =8V,V _{GS} =0V,	-	330	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	140	-	PF
Turn-on Delay Time	td(on)		-	10	20	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =1A	-	11	25	nS
Turn-Off Delay Time	td(off)	$V_{\text{DD}} = 10V, I_{\text{D}} = 1A$ $V_{\text{GS}} = 4.5V, R_{\text{GEN}} = 6\Omega$	-	35	70	nS
Turn-Off Fall Time	t _f		-	30	60	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =6A,	-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	1.5	-	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	1.7	A

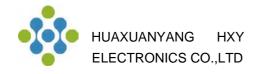
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Characteristics

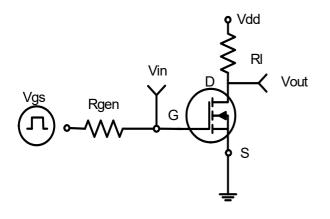
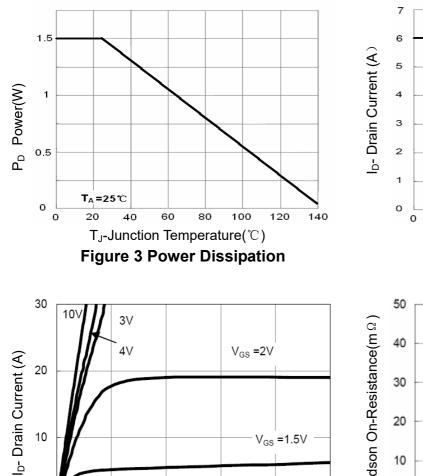


Figure 1:Switching Test Circuit



V_{GS} =1.5V

4

5

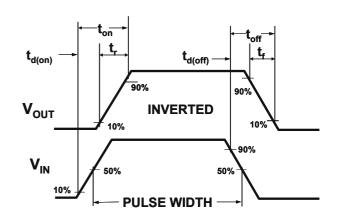
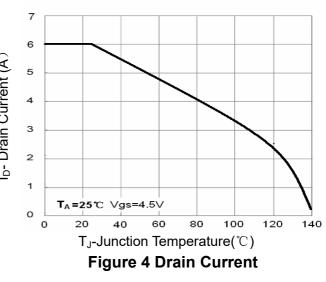


Figure 2:Switching Waveforms



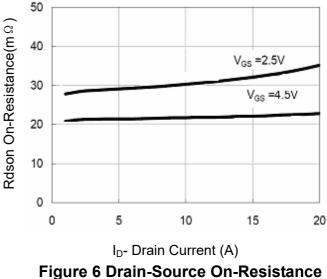


Figure 5 Output Characteristics

Vds Drain-Source Voltage (V)

3

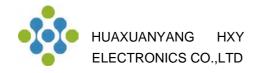
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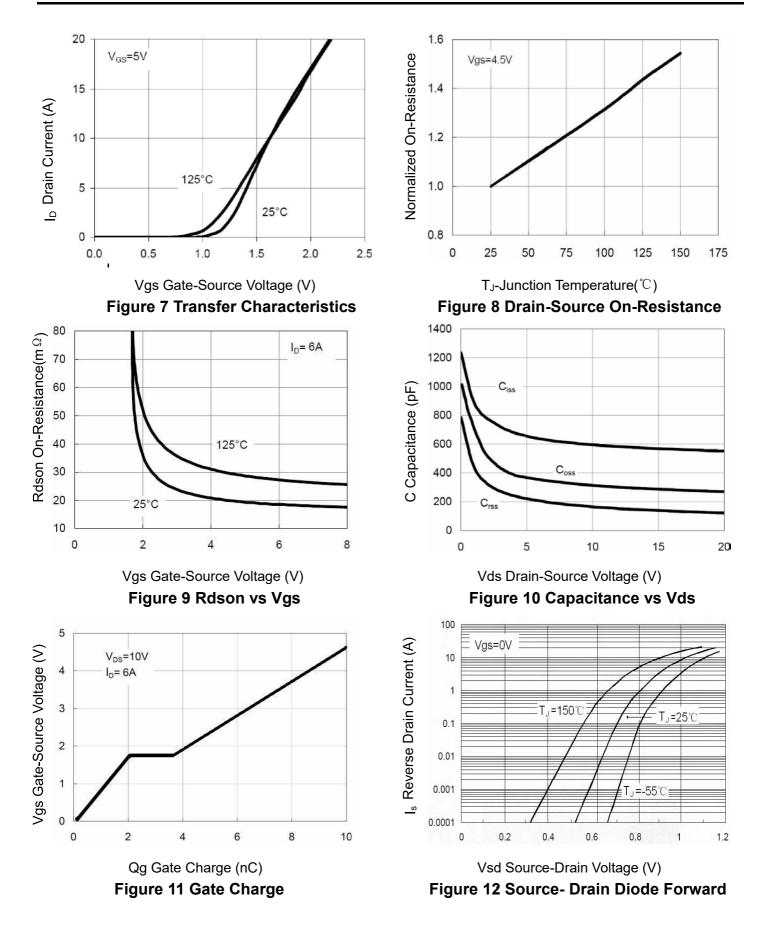
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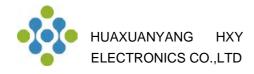
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SMC8205AGW Dual N-Channel Enhancement Mode MOSFET





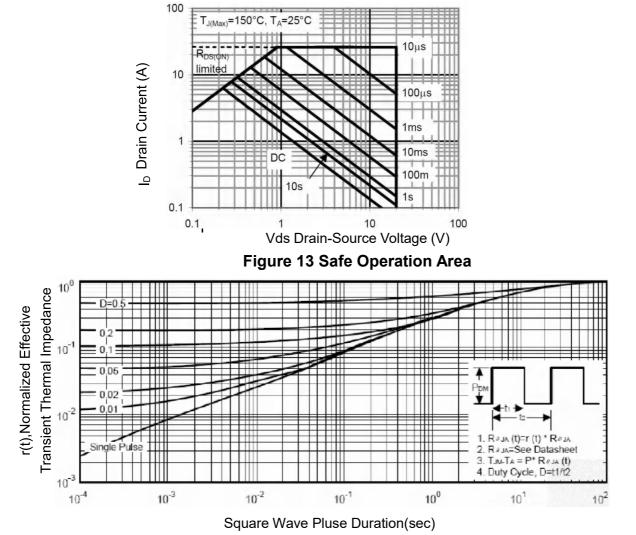
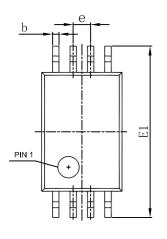
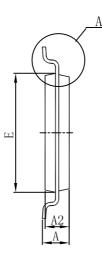


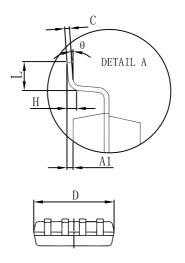
Figure 14 Normalized Maximum Transient Thermal Impedance



TSSOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3.100	0.114	0.122	
Е	4.300	4.500	0.169	0.177	
b	0.190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6.250	6.550	0.246	0.258	
Α		1.200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0.150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1°	7 °	



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